

MJE1123

**Bipolar Power PNP
Low Dropout Regulator
Transistor**

**PNP LOW DROPOUT
TRANSISTOR
4.0 AMPERES
40 VOLTS**

The MJE1123 is an applications specific device designed to provide low-dropout linear regulation for switching-regulator post regulators, battery powered systems and other applications. The MJE1123 is fully specified in the saturation region and exhibits the following main features:

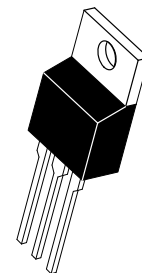
- High Gain Limits Base-Drive Losses to only 1-2% of Circuit Output Current
- Gain is 100 Minimum at $I_C = 1.0$ Amp, $V_{CE} = 7.0$ Volts
- Excellent Saturation Voltage Characteristic, 0.2 Volts Maximum at 1.0 Amp

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted.)

Rating	Symbol	Value	Unit
Collector-Emitter Sustaining Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CB}	50	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current — Continuous	I_C	4.0	Adc
— Peak	I_{CM}	8.0	
Base Current — Continuous	I_B	4.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	75 0.6	Watts W/ $^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{stg}	- 65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case	$R_{\theta JC}$	1.67	$^\circ\text{C/W}$
— Junction to Ambient	$R_{\theta JA}$	70	
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 seconds	T_L	275	$^\circ\text{C}$



**CASE 221A-06
TO-220AB**

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS*

Collector-Emitter Sustaining Voltage ($I_C = 1.0$ mA, $I = 0$)	$V_{CEO(sus)}$	40	65	—	Vdc
Emitter-Base Voltage ($I_E = 100$ μA)	V_{EBO}	7.0	11	—	Vdc
Collector Cutoff Current ($V_{CE} = 7.0$ Vdc, $I_B = 0$) ($V_{CE} = 20$ Vdc, $I_B = 0$)	I_{CEO}	— —	— —	100 250	μAdc

ON CHARACTERISTICS*

Collector-Emitter Saturation Voltage ($I_C = 1.0$ Adc, $I_B = 20$ mAdc) ($I_C = 1.0$ Adc, $I_B = 50$ mAdc) ($I_C = 1.0$ Adc, $I_B = 120$ mAdc) ($I_C = 2.0$ Adc, $I_B = 50$ mAdc) ($I_C = 2.0$ Adc, $I_B = 120$ mAdc) ($I_C = 4.0$ Adc, $I_B = 120$ mAdc)	$V_{CE(sat)}$	— — — — — —	0.16 0.13 0.10 0.25 0.20 0.45	0.30 0.25 0.20 0.40 0.35 0.75	Vdc
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* Indicates Pulse Test: Pulse Width = 300 μs max, Duty Cycle = 2%.

(continued)

ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS* (continued)					
Base-Emitter Saturation Voltage ($I_C = 1.0 \text{ Adc}, I_B = 20 \text{ mAdc}$) ($I_C = 2.0 \text{ Adc}, I_B = 50 \text{ mAdc}$) ($I_C = 4.0 \text{ Adc}, I_B = 120 \text{ mAdc}$)	$V_{BE(sat)}$	—	0.77 0.87 1.00	0.95 1.20 1.40	Vdc
DC Current Gain ($I_C = 1.0 \text{ Adc}, V_{CE} = 7.0 \text{ Vdc}$) ($I_C = 1.0 \text{ Adc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 2.0 \text{ Adc}, V_{CE} = 7.0 \text{ Vdc}$) ($I_C = 2.0 \text{ Adc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 4.0 \text{ Adc}, V_{CE} = 7.0 \text{ Vdc}$) ($I_C = 4.0 \text{ Adc}, V_{CE} = 10 \text{ Vdc}$)	h_{FE}	100 100 75 80 45 45	170 180 120 140 75 79	225 225 170 180 100 100	—
Base-Emitter On Voltage ($I_C = 1.0 \text{ Adc}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 2.0 \text{ Adc}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 4.0 \text{ Adc}, V_{CE} = 1.0 \text{ Vdc}$)	$V_{BE(on)}$	—	0.75 0.84 0.90	0.90 1.00 1.20	Vdc

DYNAMIC CHARACTERISTICS

Current-Gain — Bandwidth Product ($I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f = 1.0 \text{ MHz}$)	f_T	5.0	11.5	—	MHz
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* Indicates Pulse Test: Pulse Width = 300 μs max, Duty Cycle = 2%.

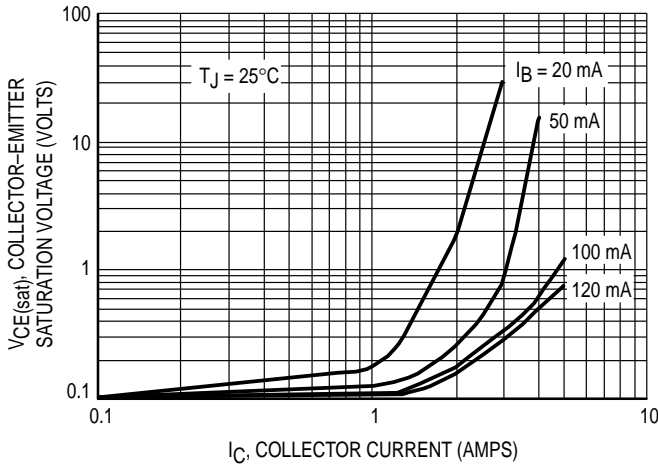


Figure 1. Saturation Voltage versus Collector Current as a Function of Base Drive

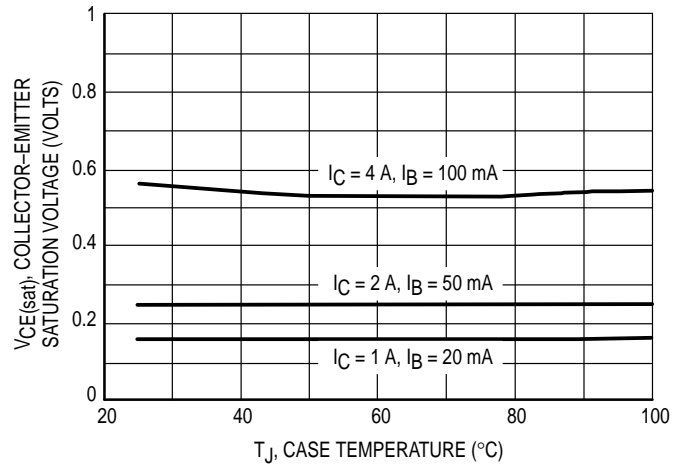


Figure 2. Saturation Voltage versus Temperature

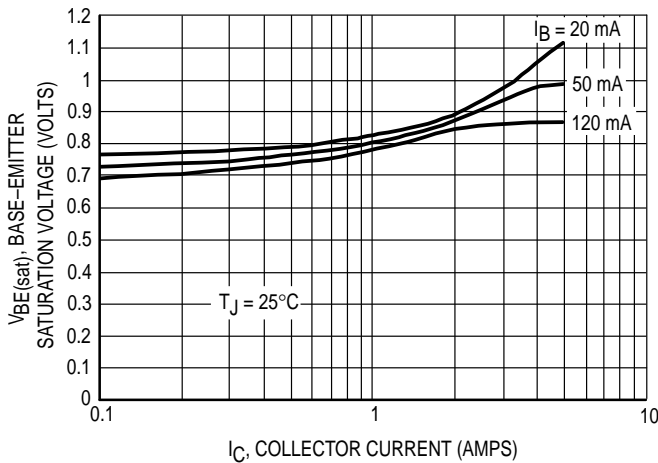


Figure 3. Base-Emitter Saturation Voltage versus Collector Current as a Function of Base Drive

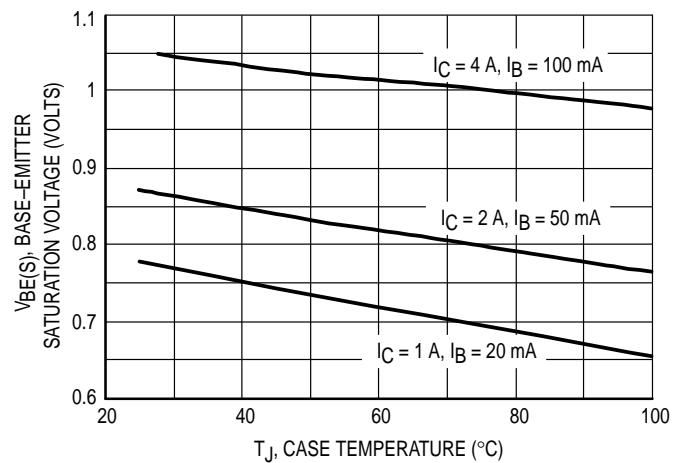


Figure 4. Base-Emitter Saturation Voltage versus Temperature

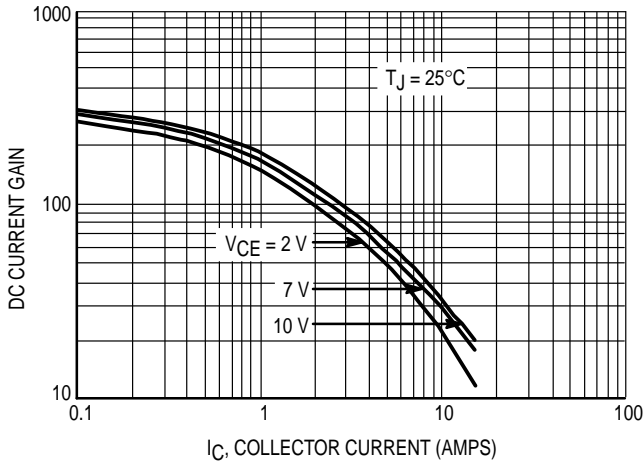


Figure 5. DC Current Gain

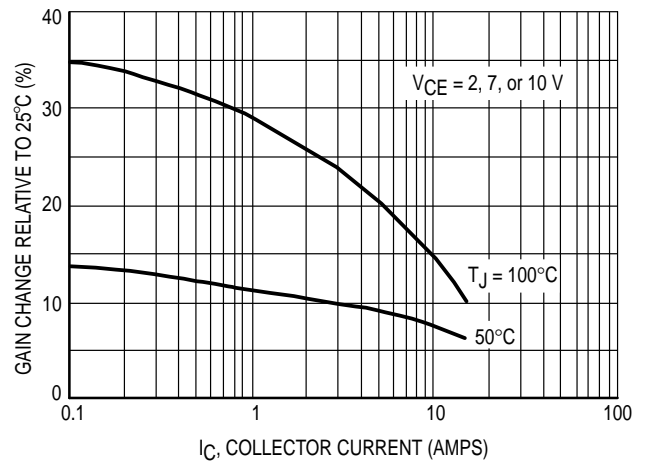


Figure 6. DC Current Gain Variation

TYPICAL LOW PASS TRANSISTOR APPLICATION

The MJE1123 was designed to operate as a low pass transistor in conjunction with the LT1123 offered by Linear Technology Corporation. Together they provide several excellent advantages:

- A dropout voltage below 50 mV at 1.0 amp, increasing to only 225 mV at 4.0 amps, typically.
- Line and load regulation are within 5.0 mV.
- Initial output accuracy is better than 1 percent.
- Full short circuit protection is included.
- Base drive loss is less than 2% of output current . . . even at 4.0 full amps output.
- The high gain and excellent collector-emitter saturation voltage make the combination better than monolithic devices.

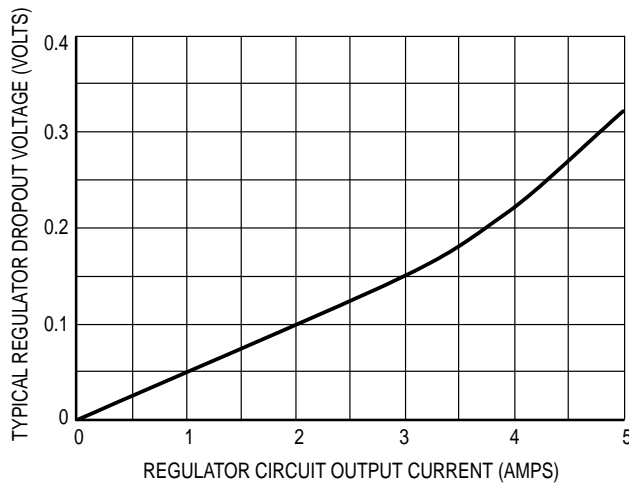
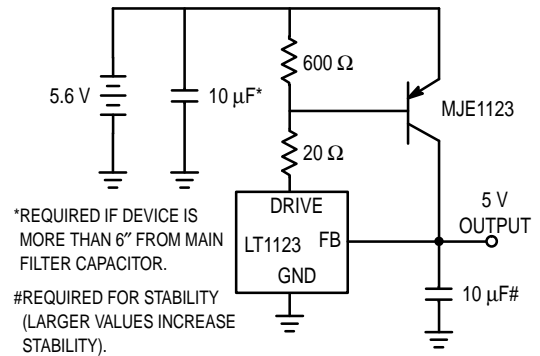


Figure 7. Typical Dropout Voltage of a MJE1123 and LT1123 Circuit

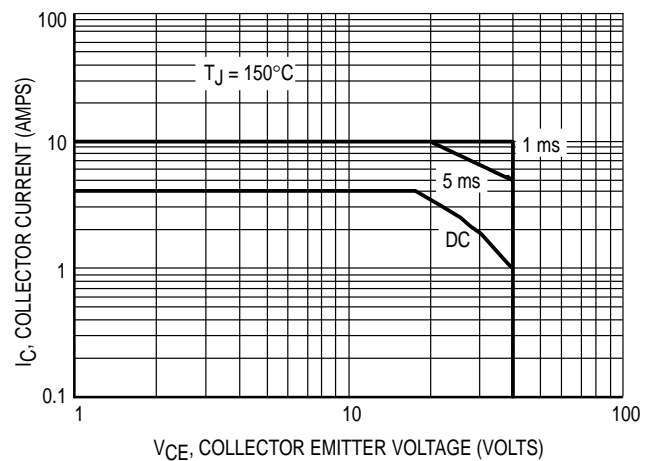


Figure 8. Maximum Forward Bias Safe Operating Area

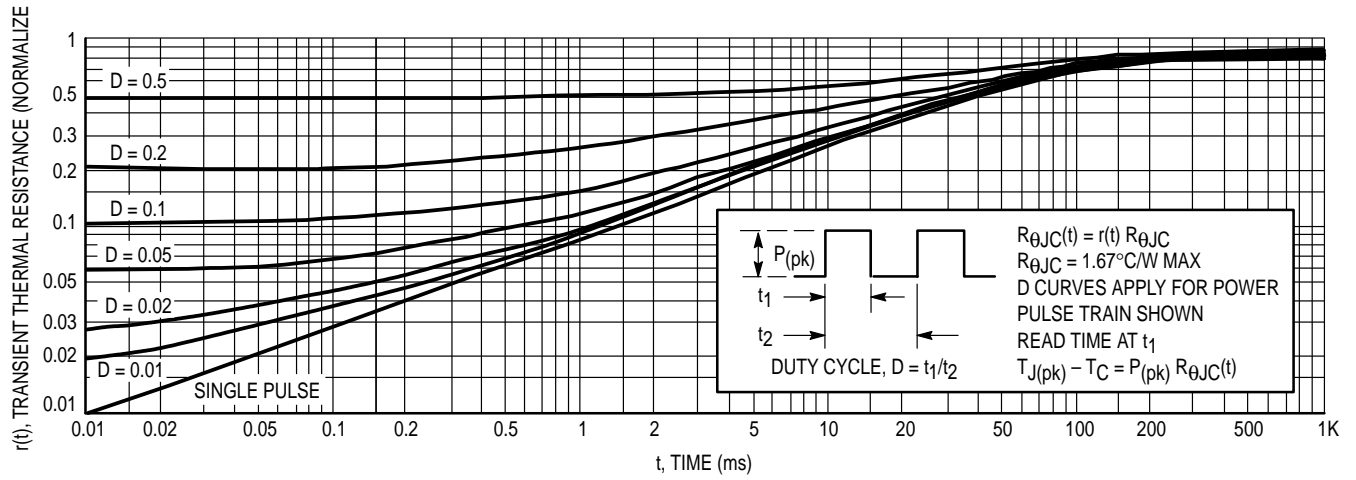
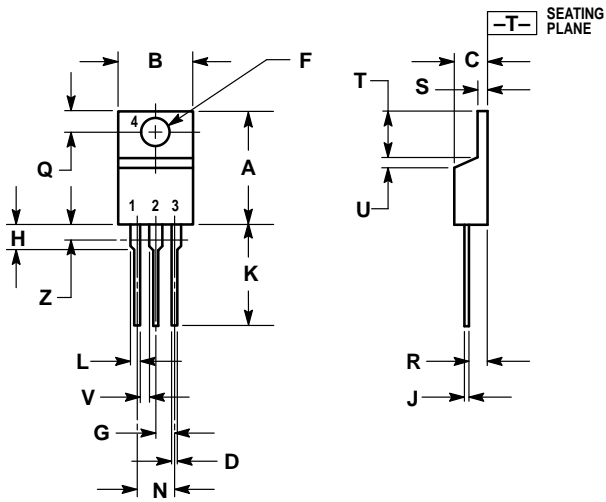


Figure 9. Typical Thermal Response

PACKAGE DIMENSIONS



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

- STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

CASE 221A-06
 TO-220AB
 ISSUE Y

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How to reach us:

USA / EUROPE: Motorola Literature Distribution;
P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki,
6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609
INTERNET: <http://Design-NET.com>

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

